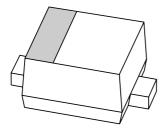
# DISCRETE SEMICONDUCTORS

# DATA SHEET



# 1PS79SB31 Schottky barrier diode

Product data sheet 2002 Jan 11



# Schottky barrier diode

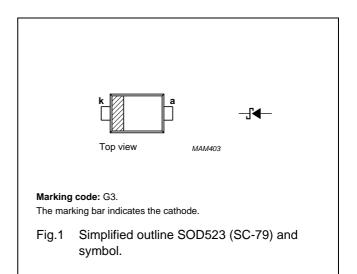
1PS79SB31

#### **FEATURES**

- Very low forward voltage
- · Guard ring protected
- Ultra small SMD package.

## **APPLICATIONS**

- Ultra high-speed switching
- Voltage clamping
- Protection circuits
- Low current rectification
- Low power consumption applications (e.g. hand-held devices).



# **DESCRIPTION**

Planar Schottky barrier diode in a SOD523 (SC-79) ultra small SMD plastic package.

## **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage		_	30	V
I <sub>F</sub>	continuous forward current		_	200	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ s}; \ \delta \le 0.5$	=	300	mA
I <sub>FSM</sub>	non-repetitive peak forward current	t = 8.3 ms half sine wave; JEDEC method	-	1000	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

# Schottky barrier diode

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# **ELECTRICAL CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>F</sub>	forward voltage	see Fig.2;			
		I <sub>F</sub> = 0.1 mA	130	190	mV
		I <sub>F</sub> = 1 mA	190	250	mV
		I <sub>F</sub> = 10 mA	255	300	mV
		I <sub>F</sub> = 100 mA	355	410	mV
		I <sub>F</sub> = 200 mA	420	500	mV
I <sub>R</sub>	continuous reverse current	V <sub>R</sub> = 10 V; note 1; see Fig.3	2.5	30	μΑ
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; see Fig.4	20	25	pF

# Note

1. Pulse test:  $t_p$  = 300  $\mu$ s;  $\delta$  = 0.02.

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to	note 1	450	K/W
	ambient			

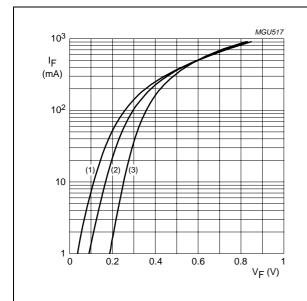
# Note

1. Refer to SC-79 (SOD523) standard mounting conditions.

# Schottky barrier diode

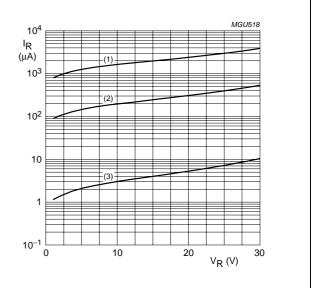
# 1PS79SB31

# **GRAPHICAL DATA**



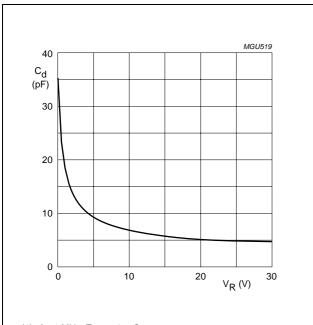
- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

Fig.2 Forward current as a function of forward voltage; typical values.



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \,^{\circ}C$ .

Fig.3 Reverse current as a function of reverse voltage; typical values.



(1) f = 1 MHz;  $T_{amb} = 25 \, ^{\circ}\text{C}$ .

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

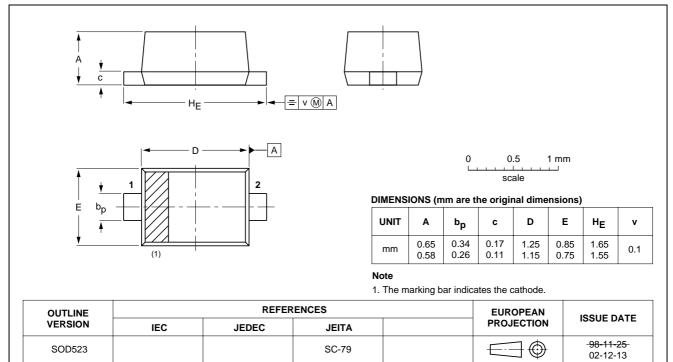
# Schottky barrier diode

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# **PACKAGE OUTLINE**

# Plastic surface mounted package; 2 leads

**SOD523** 



# Schottky barrier diode

1PS79SB31

#### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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## **Contact information**

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